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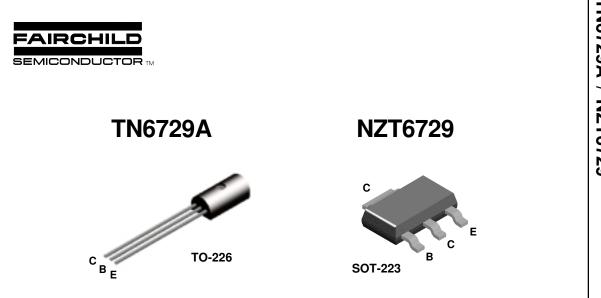
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## **PNP General Purpose Amplifier**

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 800 mA. Sourced from Process 79.

### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	1.0	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations. 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units	
		TN6729A	*NZT6729		
P <sub>D</sub>	Total Device Dissipation	1.0	1.0	W	
	Derate above 25°C	8.0	8.0	mW/∘C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	125	°C/W	

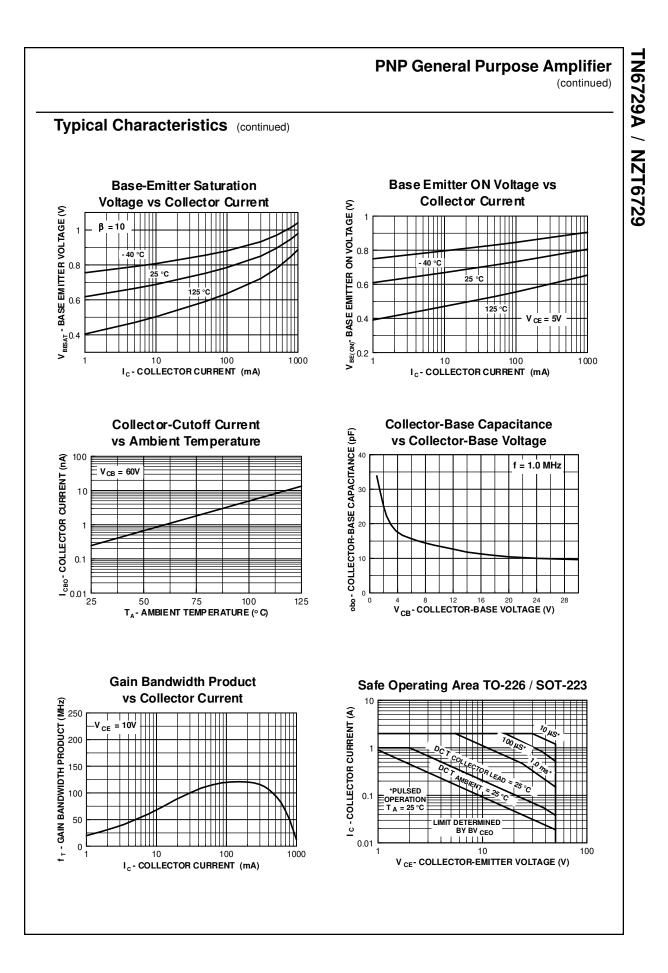
\*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

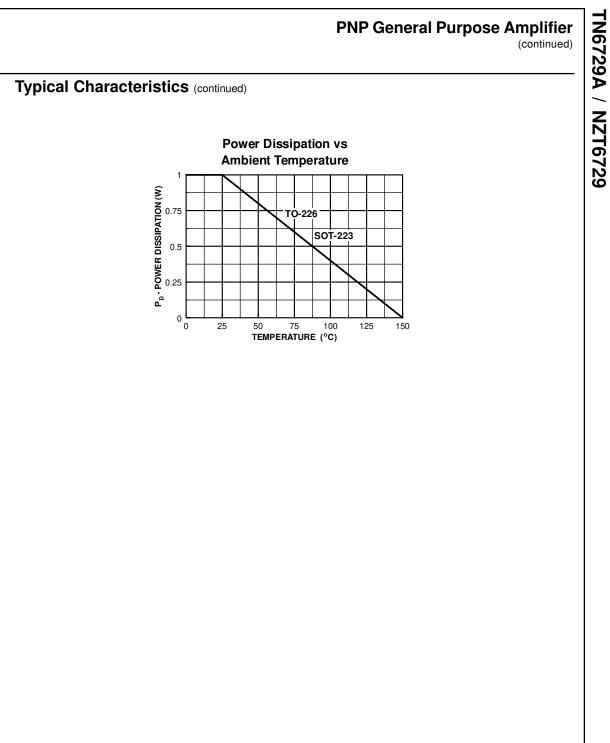
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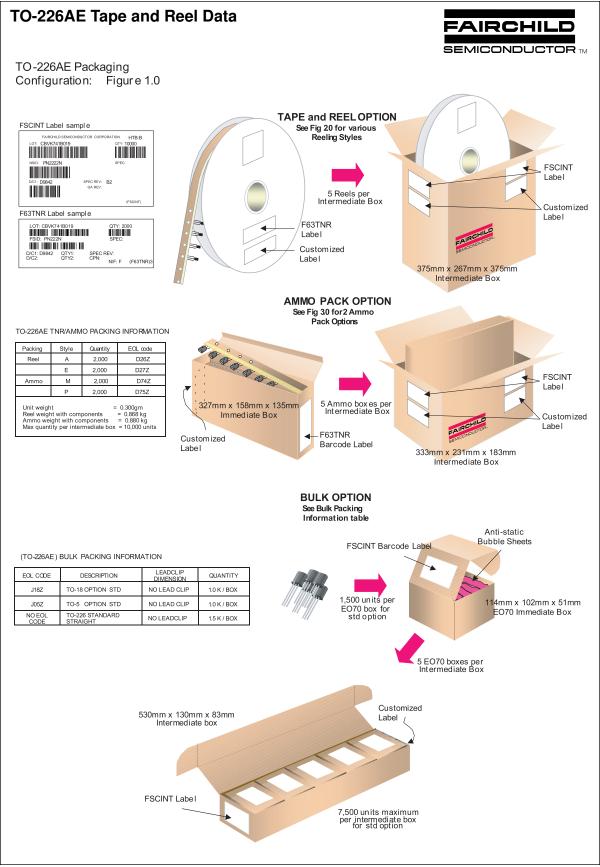
# PNP General Purpose Amplifier

V(BR)CEO (   V(BR)CBO (   V(BR)EBO (   IcBO (   IeBO (   ON CHARAC (   h <sub>FE</sub> I	ACTERISTICS Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current	$\begin{split} I_{C} &= 1.0 \text{ mA}, I_{B} = 0 \\ I_{C} &= 100 \ \mu\text{A}, I_{E} = 0 \\ I_{E} &= 1.0 \ \text{mA}, I_{C} = 0 \\ V_{CB} &= 60 \ \text{V}, I_{E} = 0 \\ V_{EB} &= 5.0 \ \text{V}, I_{C} = 0 \end{split}$	80 80 5.0		V
V(BR)CEO (   V(BR)CBO (   V(BR)EBO (   IcBO (   IeBO (   ON CHARAC (   h <sub>FE</sub> I	Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current	$\begin{split} I_{C} &= 100 \; \mu A, \; I_{E} = 0 \\ I_{E} &= 1.0 \; m A, \; I_{C} = 0 \\ V_{CB} &= 60 \; V, \; I_{E} = 0 \end{split}$	80		
V(BR)CBO (   V(BR)CBO I   IcBO I   IcBO (   NCHARA(   NCHARA(   h <sub>FE</sub> I	Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current	$\begin{split} I_{C} &= 100 \; \mu A, \; I_{E} = 0 \\ I_{E} &= 1.0 \; m A, \; I_{C} = 0 \\ V_{CB} &= 60 \; V, \; I_{E} = 0 \end{split}$	80		V
V <sub>(BR)EBO</sub> I I <sub>CBO</sub> ( I <sub>EBO</sub> I ON CHARA( h <sub>FE</sub> I	Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current	$I_{E} = 1.0 \text{ mA}, I_{C} = 0$ $V_{CB} = 60 \text{ V}, I_{E} = 0$			
CBO ( EBO I DN CHARAG	Collector-Cutoff Current Emitter-Cutoff Current	$V_{CB} = 60 \text{ V}, \text{ I}_{E} = 0$			V
DN CHARAC	Emitter-Cutoff Current			0.1	μA
ı <sub>fe</sub> I	CTERISTICS*			10	μA
ı <sub>fe</sub> I					
	DC Current Gain	I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 1.0 V	80		
		I <sub>C</sub> = 250 mA, V <sub>CE</sub> = 1.0 V	50	250	
		$I_{\rm C} = 500 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$	20	0.5	V
/ <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 250 \text{ mA}, I_{\rm B} = 10 \text{ mA}$ $I_{\rm C} = 250 \text{ mA}, I_{\rm B} = 25 \text{ mA}$		0.5 0.35	v
/ <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{C} = 250 \text{ mA}, I_{B} = 25 \text{ mA}$ $I_{C} = 250 \text{ mA}, V_{CE} = 1.0 \text{ V}$		1.2	V
*Pulse Test: Pulse	Collector-Base Capacitance a Width $\leq$ 300 µs, Duty Cycle $\leq$ 1.0% s (V) and currents (A) are negative polarity for PNP	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		30	pF
Тур	Characteristics pical Pulsed Current Gain vs Collector Current	Collector- ᢓᢩ Voltage vs			
200 C					
P <sup>2</sup> − 40 000 000 000 000 000 000 000 000 00	V <sub>CE</sub> = 1.0	$\vec{v}$ $\vec{h}$ $\beta = 10$			
H 150 125				25 °C	
1 25 °		<b>6</b> 0.1			
	<u>;</u>	E E		125 °C	
	Ĭ				
50 - 40°		V Voltage vs $\gamma$ $\beta = 10$ $\beta = 10$			$+ \square$

TN6729A / NZT6729

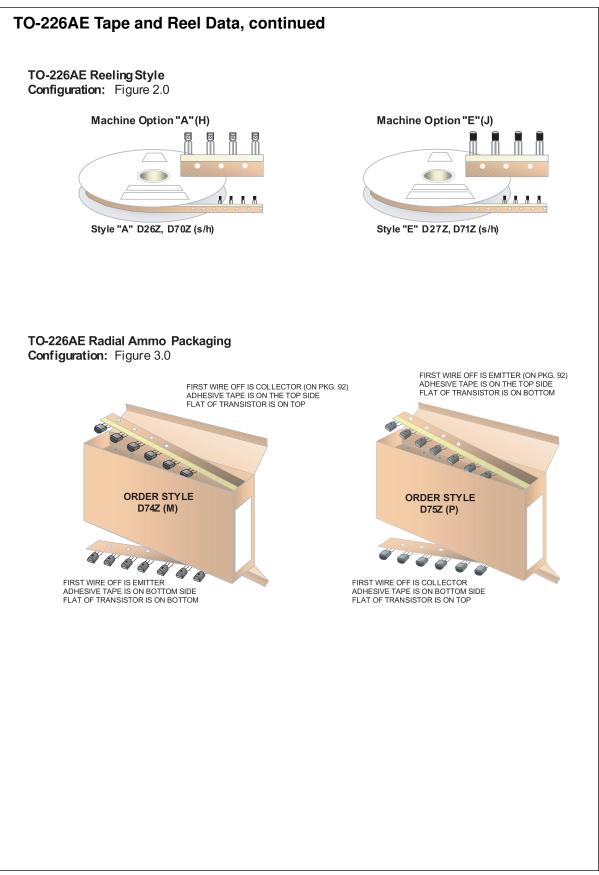


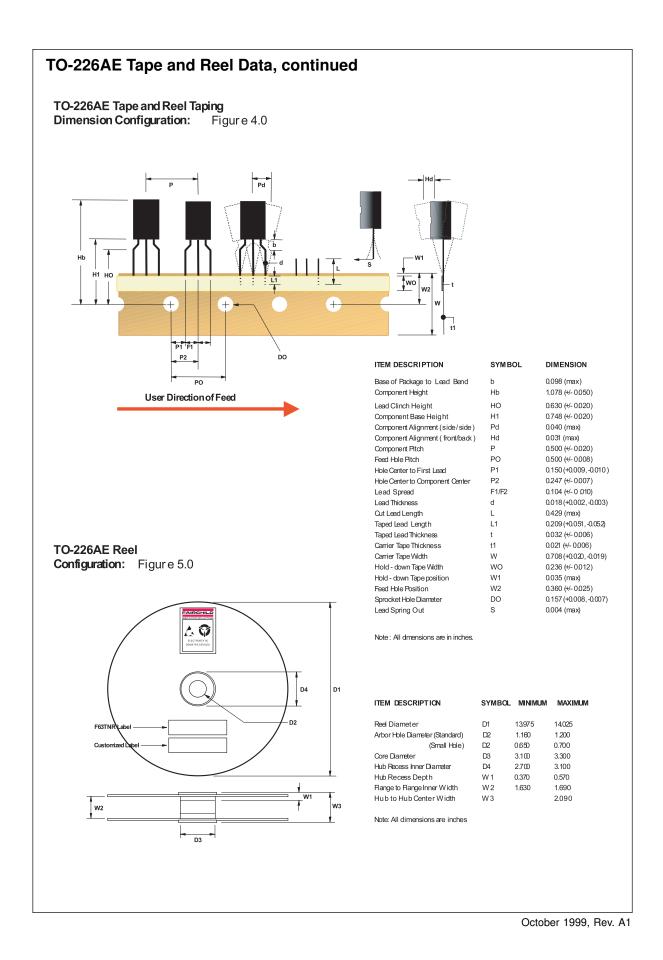


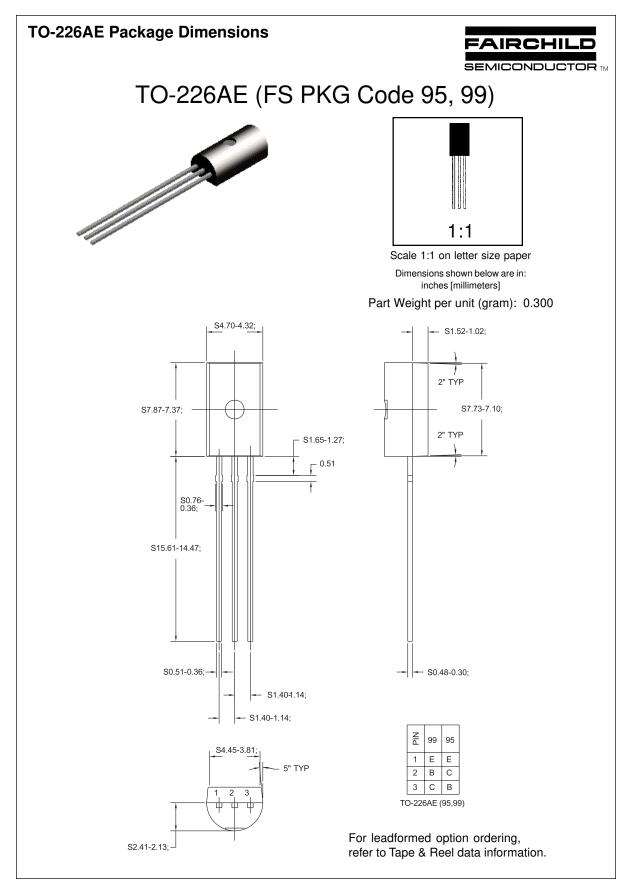


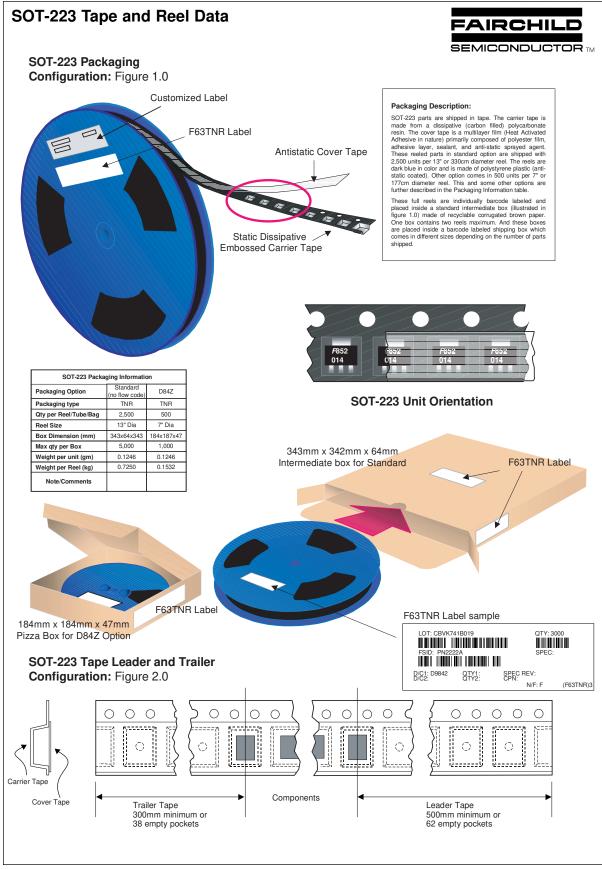
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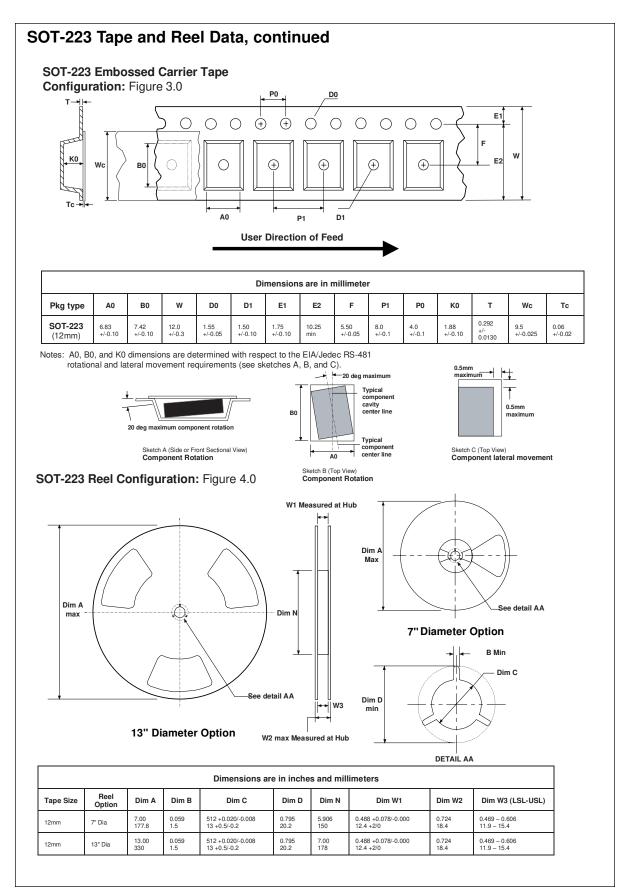


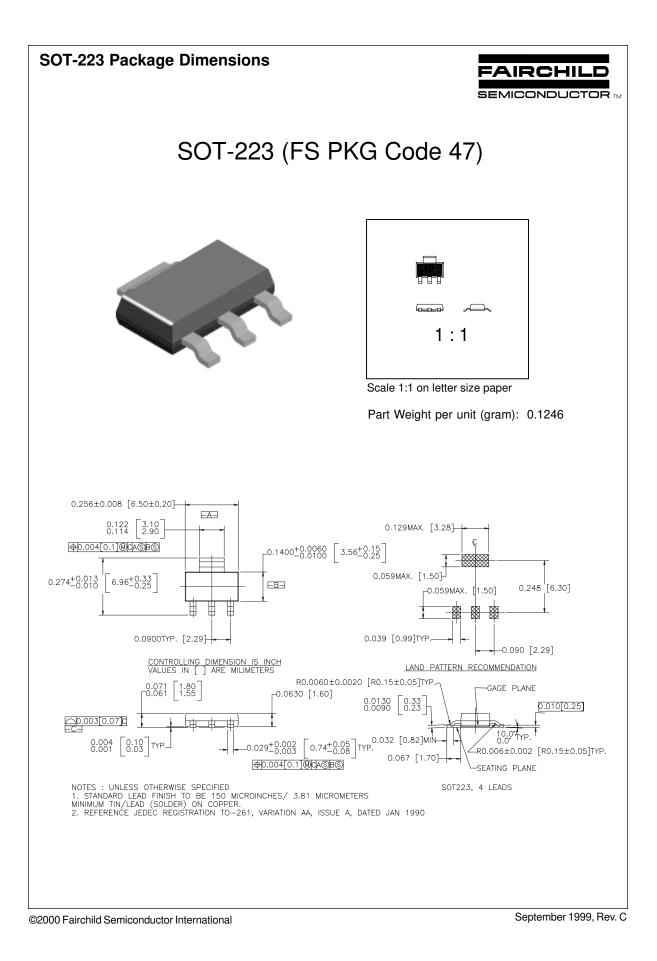




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